
2SB562

Silicon PNP Epitaxial

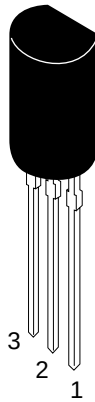
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Application

- Low frequency power amplifier
- Complementary pair with 2SD468

Outline

TO-92MOD



1. Emitter
2. Collector
3. Base

Absolute Maximum Ratings (Ta = 25°C)

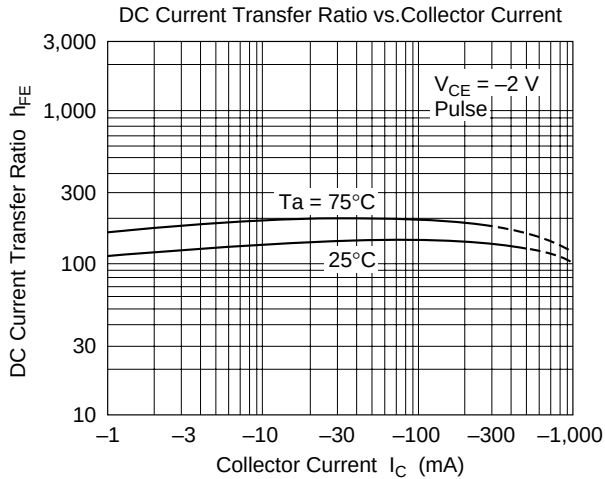
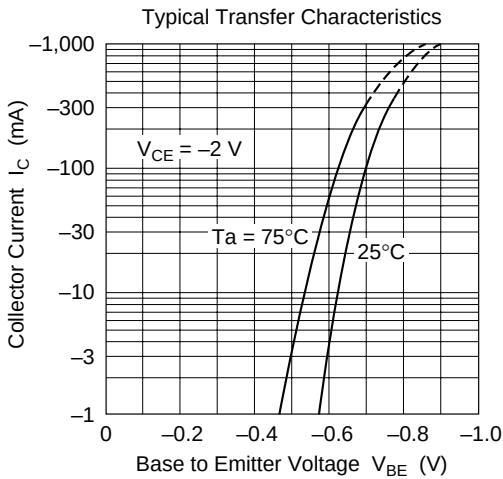
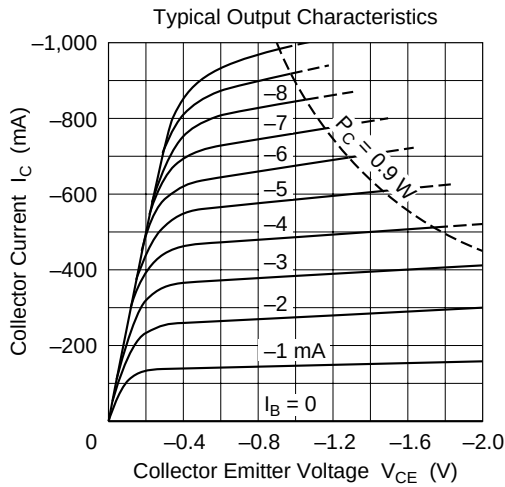
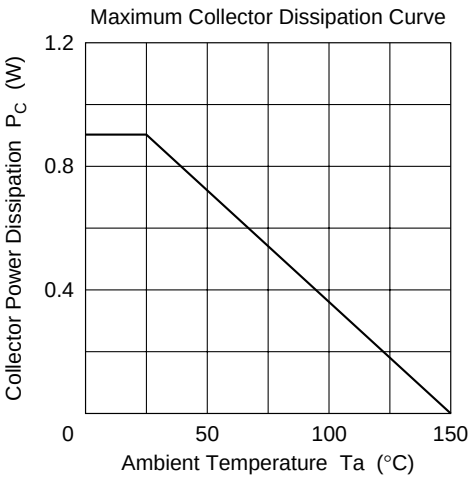
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	−25	V
Collector to emitter voltage	V_{CEO}	−20	V
Emitter to base voltage	V_{EBO}	−5	V
Collector current	I_C	−1.0	A
Collector peak current	$i_{C(peak)}$	−1.5	A
Collector power dissipation	P_C	0.9	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

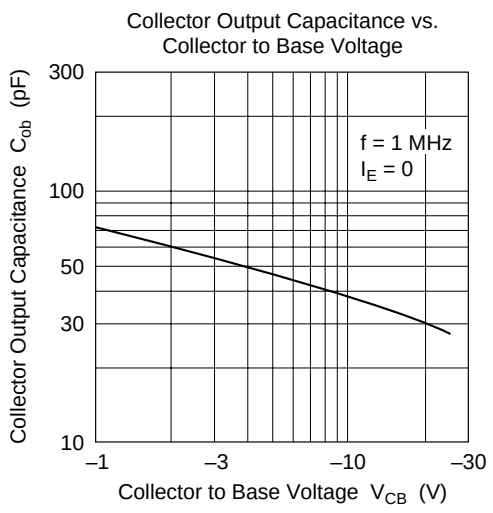
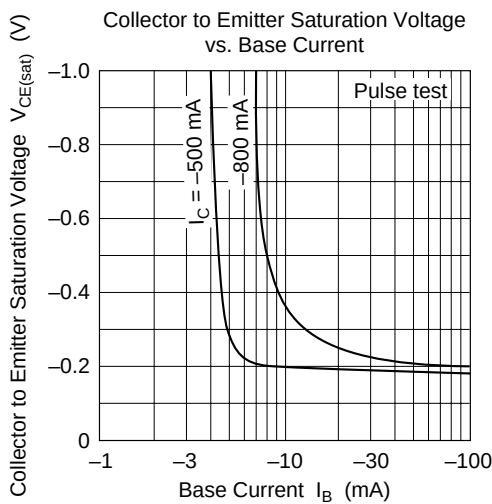
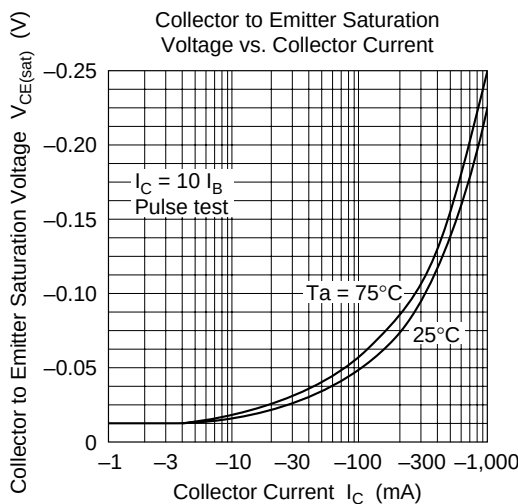
Electrical Characteristics (Ta = 25°C)

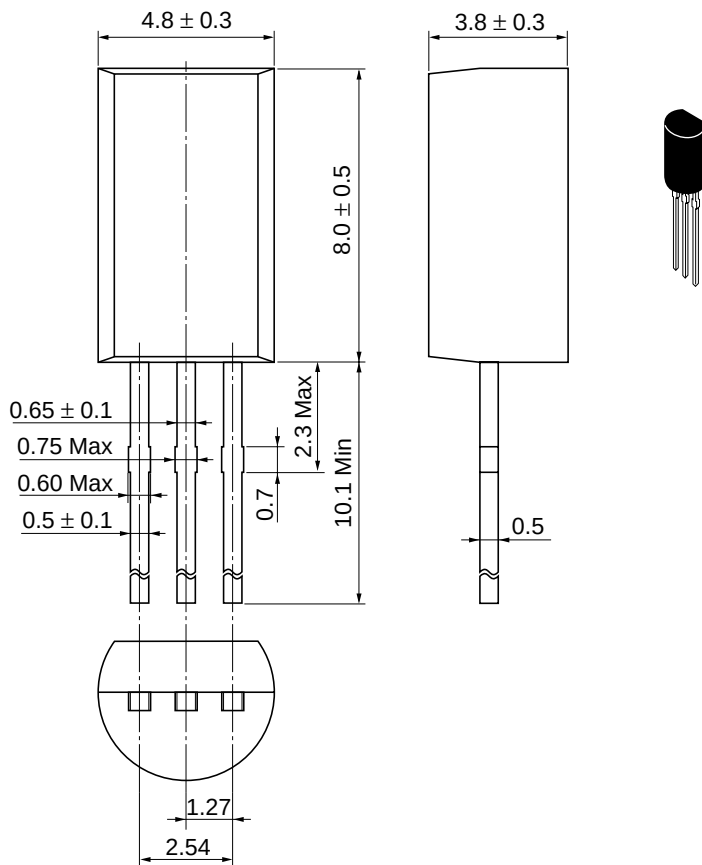
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	−25	—	—	V	$I_C = -10\ \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	−20	—	—	V	$I_C = -1\ mA, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	−5	—	—	V	$I_E = -10\ \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	−1.0	μA	$V_{CB} = -20\ V, I_E = 0$
DC current transfer ratio	h_{FE}^{*1}	85	—	240		$V_{CE} = -2\ V,$ $I_C = -0.5\ A$ (Pulse test)
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	−0.2	−0.5	V	$I_C = -0.8\ A,$ $I_B = -0.08\ A$ (Pulse test)
Base to emitter voltage	V_{BE}	—	−0.8	−1.0	V	$V_{CE} = -2\ V,$ $I_C = -0.5\ A$ (Pulse test)
Gain bandwidth product	f_T	—	350	—	MHz	$V_{CE} = -2\ V,$ $I_C = -0.5\ A$ (Pulse test)
Collector output capacitance	C_{ob}	—	38	—	pF	$V_{CB} = -10\ V, I_E = 0$ $f = 1\ MHz$

Note: 1. The 2SB562 is grouped by h_{FE} as follows.

B	C
85 to 170	120 to 240







Hitachi Code	TO-92 Mod
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.35 g

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